



DATA SHEET

MOSFETs

Order code	Manufacturer code	Description
47-0156	n/a	ZVN2106A N CHANNEL MOSFET

MOSFETs

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The enclosed information is believed to be correct. Information may change 'without notice' due to product improvement. Users should ensure that the product is suitable for their use. E. & O. E.

Revision A
04/07/2003

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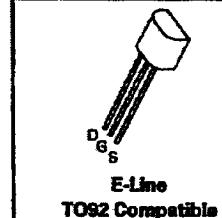
**N-CHANNEL ENHANCEMENT
MODE VERTICAL DMOS FET**

ISSUE 2 - MARCH 94

FEATURES

- * 60 Volt V_{DS}
- * $R_{DS(on)}=2\Omega$

ZVN2106A



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current at $T_{amb}=25^\circ C$	I_D	450	mA
Pulsed Drain Current	I_{DM}	8	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^\circ C$	P_{tot}	700	mW
Operating and Storage Temperature Range	$T_f; T_{stg}$	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	60		V	$I_D=1mA, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8	2.4	V	$I_D=1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		20	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}		500 100	nA μA	$V_{DS}=60V, V_{GS}=0$ $V_{DS}=48V, V_{GS}=0V, T=125^\circ C$ (2)
On-State Drain Current(1)	$I_{D(on)}$	2		A	$V_{DS}=18V, V_{GS}=10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		2	Ω	$V_{GS}=10V, I_D=1A$
Forward Transconductance (1)(2)	G_{fs}	300		mS	$V_{DS}=18V, I_D=1A$
Input Capacitance (2)	C_{iss}		75	pF	$V_{DS}=18V, V_{GS}=0V, f=1MHz$
Common Source Output Capacitance (2)	C_{oss}		45	pF	
Reverse Transfer Capacitance (2)	C_{trs}		20	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		7	ns	$V_{DD}=18V, I_D=1A$
Rise Time (2)(3)	t_r		8	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		12	ns	
Fall Time (2)(3)	t_f		15	ns	

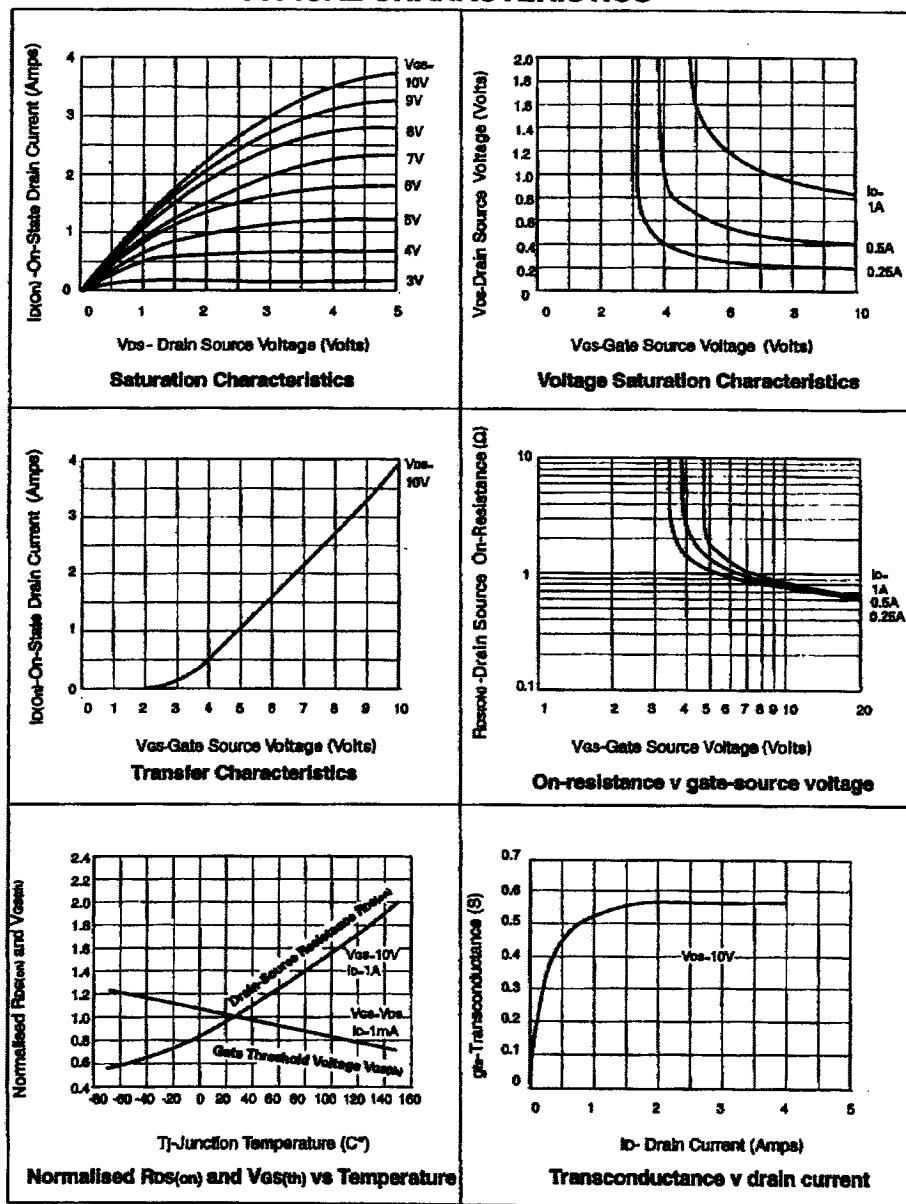
(1) Measured under pulsed conditions. Width=300μs. Duty cycle ≤2%

(2) Sample test.

(3) Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator

ZVN2106A

TYPICAL CHARACTERISTICS



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TYPICAL CHARACTERISTICS

